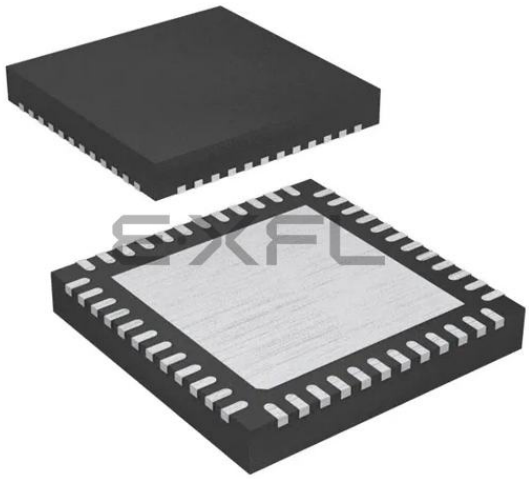

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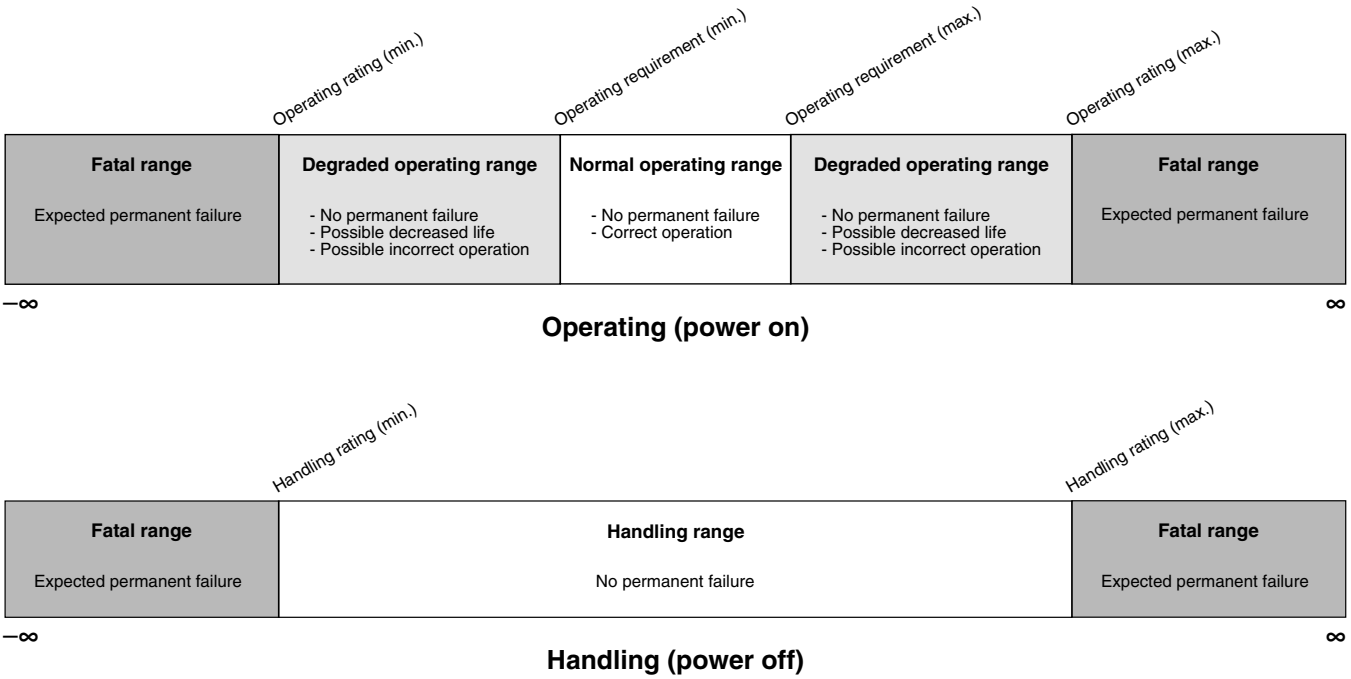
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	33
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN-EP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dn64vft5

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

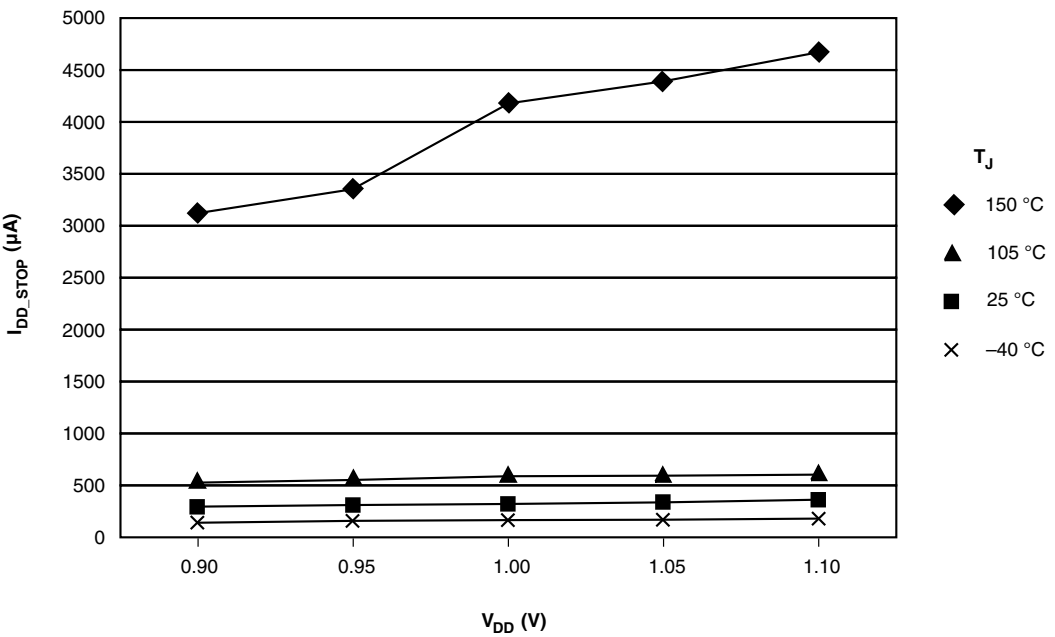
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V

Table continues on the next page...

Symbol	Description	Min.	Max.	Unit
I_{DD}	Digital supply current	—	155	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, and XTAL)	–0.3	V_{DD} + 0.3	V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{BAT}	RTC battery supply voltage	–0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

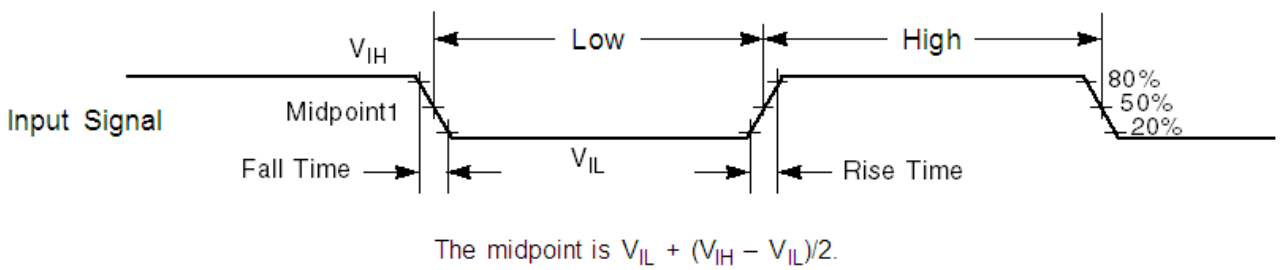


Figure 1. Input signal measurement reference

All digital I/O switching characteristics assume:

1. output pins
   - have C_L=30pF loads,
   - are configured for fast slew rate (PORTx_PCRn[SRE]=0), and
   - are configured for high drive strength (PORTx_PCRn[DSE]=1)
2. input pins
   - have their passive filter disabled (PORTx_PCRn[PFE]=0)

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICIO}	I/O pin DC injection current — single pin • V_{IN} < V_{SS}-0.3V (Negative current injection) • V_{IN} > V_{DD}+0.3V (Positive current injection)	 -3 —	 — +3	 mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	 mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} (=V_{SS}-0.3V) and V_{IN} is less than V_{AIO_MAX}(=V_{DD}+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|. The positive injection current limiting resistor is calcualted as R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	

Table continues on the next page...

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	µs	1
	• VLLS0 → RUN	—	130	µs	
	• VLLS1 → RUN	—	130	µs	
	• VLLS2 → RUN	—	70	µs	
	• VLLS3 → RUN	—	70	µs	
	• LLS → RUN	—	6	µs	
	• VLPS → RUN	—	5.2	µs	
	• STOP → RUN	—	5.2	µs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					2
	• @ 1.8V	—	13.7	15.1	mA	
	• @ 3.0V	—	13.9	15.3	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3, 4
	• @ 1.8V	—	16.1	18.2	mA	
	• @ 3.0V	—	16.3	17.7	mA	
	• @ 25°C	—	16.7	18.4	mA	
	• @ 125°C					
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	7.5	8.4	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	5.6	6.4	mA	5

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	867	—	µA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.1	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V	—	509	—	µA	8
I_{DD_STOP}	Stop mode current at 3.0 V					
	• @ –40 to 25°C	—	310	426	µA	
	• @ 70°C	—	384	458	µA	
	• @ 105°C	—	629	1100	µA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ –40 to 25°C	—	3.5	22.6	µA	
	• @ 70°C	—	20.7	52.9	µA	
	• @ 105°C	—	85	220	µA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					
	• @ –40 to 25°C	—	2.1	3.7	µA	
	• @ 70°C	—	7.7	43.1	µA	
	• @ 105°C	—	32.2	68	µA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	• @ –40 to 25°C	—	1.5	2.9	µA	
	• @ 70°C	—	4.8	22.5	µA	
	• @ 105°C	—	20	37.8	µA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	• @ –40 to 25°C	—	1.4	2.8	µA	
	• @ 70°C	—	4.1	19.2	µA	
	• @ 105°C	—	17.3	32.4	µA	
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	• @ –40 to 25°C	—	0.678	1.3	µA	
	• @ 70°C	—	2.8	13.6	µA	
	• @ 105°C	—	13.6	24.5	µA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled					
	• @ –40 to 25°C	—	0.367	1.0	µA	
	• @ 70°C	—	2.4	13.3	µA	
	• @ 105°C	—	13.2	24.1	µA	

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled					
	• @ –40 to 25°C	—	0.176	0.859	µA	
	• @ 70°C	—	2.2	13.1	µA	
	• @ 105°C	—	13	23.9	µA	
I_{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V					
	• @ –40 to 25°C	—	0.19	0.22	µA	
	• @ 70°C	—	0.49	0.64	µA	
	• @ 105°C	—	2.2	3.2	µA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers					9
	• @ 1.8V					
	• @ –40 to 25°C	—	0.57	0.67	µA	
	• @ 70°C	—	0.90	1.2	µA	
	• @ 105°C	—	2.4	3.5	µA	
	• @ 3.0V					
	• @ –40 to 25°C	—	0.67	0.94	µA	
	• @ 70°C	—	1.0	1.4	µA	
	• @ 105°C	—	2.7	3.9	µA	

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50MHz core and system clock, 25MHz bus clock, and 25MHz flash clock . MCG configured for FEI mode. All peripheral clocks disabled.
3. 50MHz core and system clock, 25MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25MHz core and system clock, 25MHz bus clock, and 12.5MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

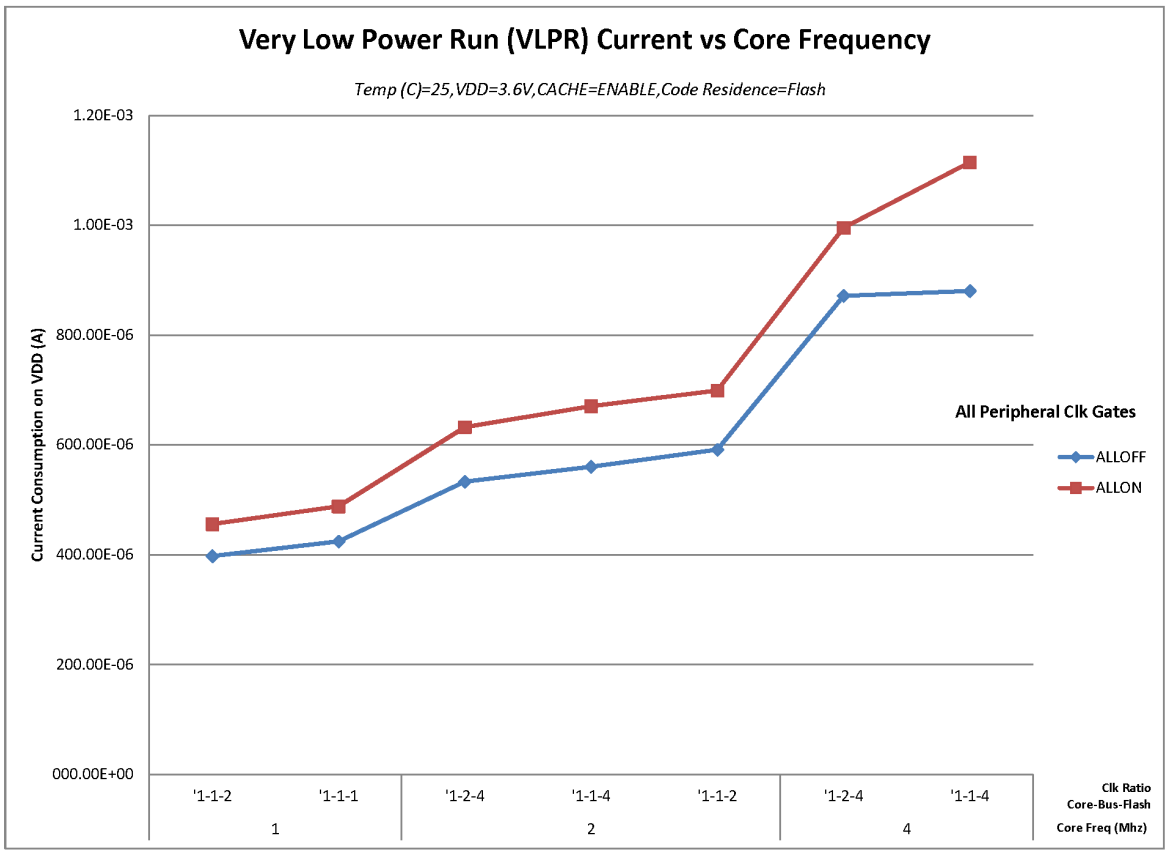


Figure 3. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 64LQFP

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	19	dBµV	1 , 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	21	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	19	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	11	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	L	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CMT, and I^2C signals.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	50	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select ($\overline{EZP\_CS}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength) • Slew disabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$ • Slew enabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$	 — — — —	 13 7 36 24	 ns ns ns ns	4

Table continues on the next page...

Board type	Symbol	Description	48 LQFP	48 QFN	Unit	Notes
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	58	66	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	40	23	°C/W	,
—	$R_{\theta JB}$	Thermal resistance, junction to board	24	11	°C/W	5
—	$R_{\theta JC}$	Thermal resistance, junction to case	18	1.4	°C/W	6
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	4	°C/W	7

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.
3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
5. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
6. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
7. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

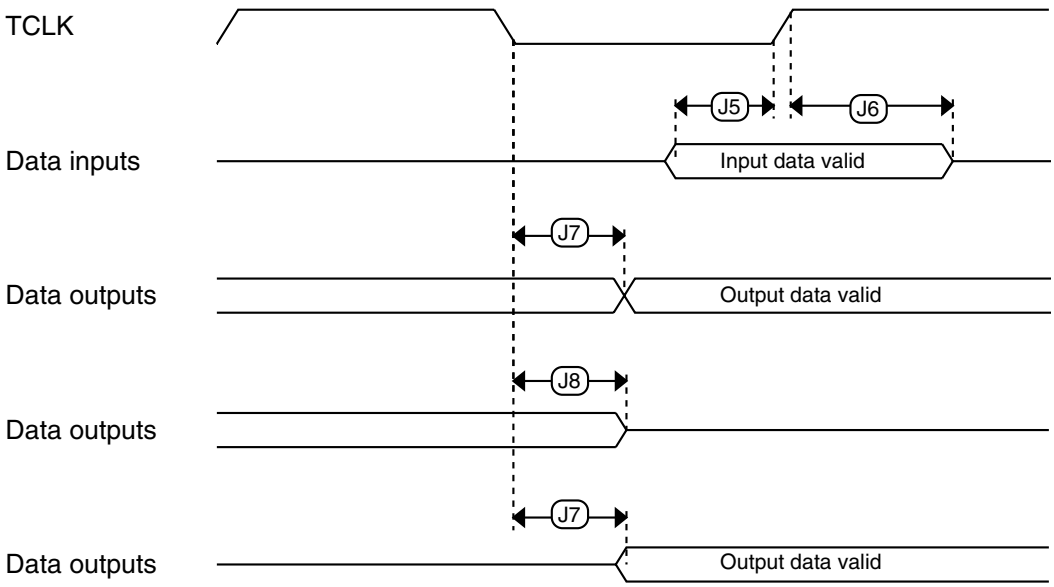


Figure 5. Boundary scan (JTAG) timing

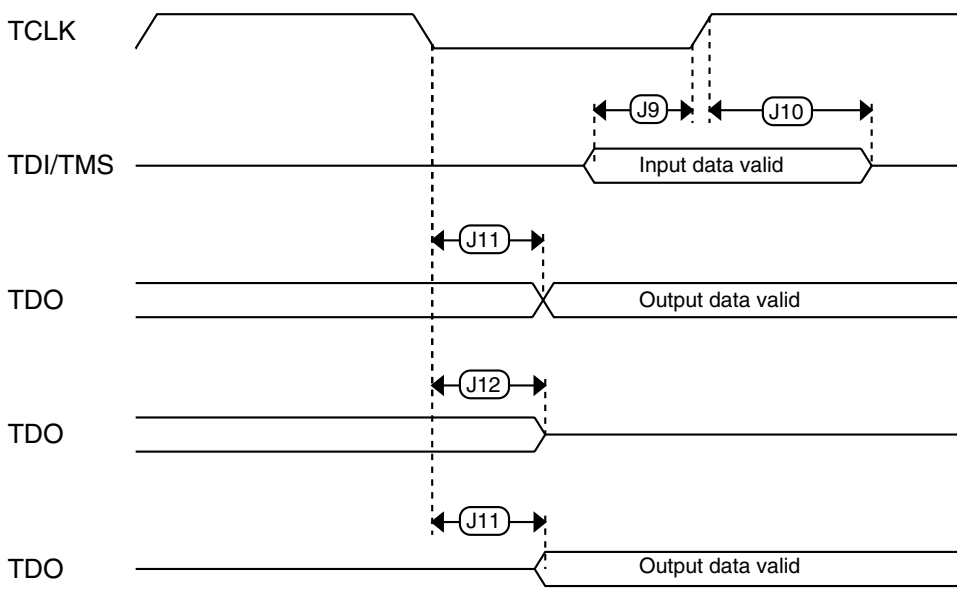


Figure 6. Test Access Port timing

Table 13. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
J_{acc_pll}	PLL accumulated jitter over 1µs (RMS)					8
	• f_{vco} = 48 MHz	—	1350	—	ps	
	• f_{vco} = 100 MHz	—	600	—	ps	
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll\_ref})$	s	9

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
3. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
6. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
7. Excludes any oscillator currents that are also consuming power while PLL is in operation.
8. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
9. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.

6.3.2.1 Oscillator DC electrical specifications

Table 14. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	

Table continues on the next page...

Table 24. 16-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
f_{ADACK}	ADC asynchronous clock source	• ADLPC=1, ADHSC=0 • ADLPC=1, ADHSC=1 • ADLPC=0, ADHSC=0 • ADLPC=0, ADHSC=1	1.2 3.0 2.4 4.4	2.4 4.0 5.2 6.2	3.9 7.3 6.1 9.5	MHz MHz MHz MHz	t_{ADACK} = 1/ f_{ADACK}
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12 bit modes • <12 bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12 bit modes • <12 bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12 bit modes • <12 bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12 bit modes • <12 bit modes	— —	-4 -1.4	-5.4 -1.8	LSB[4]	V_{ADIN} = V_{DDA} 5
E_Q	Quantization error	• 16 bit modes • ≤13 bit modes	— —	-1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16 bit differential mode • Avg=32 • Avg=4 16 bit single-ended mode • Avg=32 • Avg=4	 12.8 11.9 12.2 11.4	 14.5 13.8 13.9 13.1	 — — — —	 bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16 bit differential mode • Avg=32 16 bit single-ended mode • Avg=32	 — —	 –94 -85	 — —	 dB dB	7

Table continues on the next page...

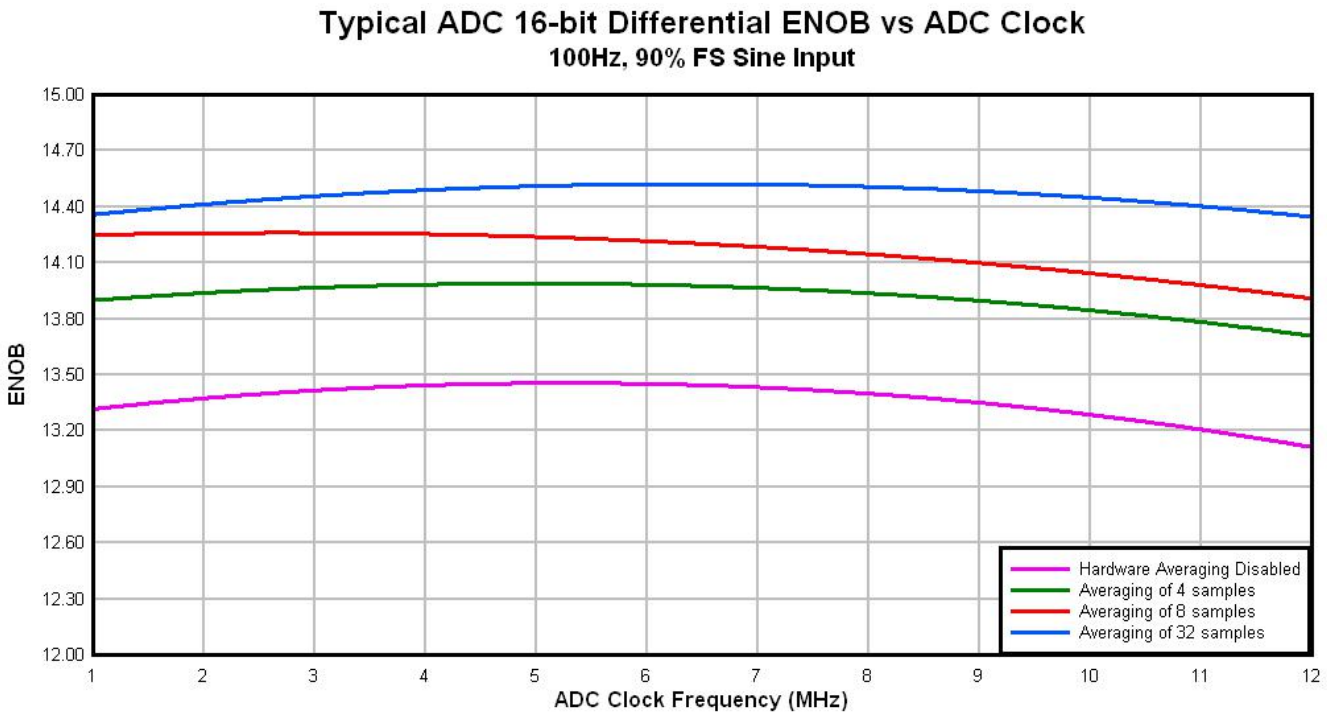


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit differential mode

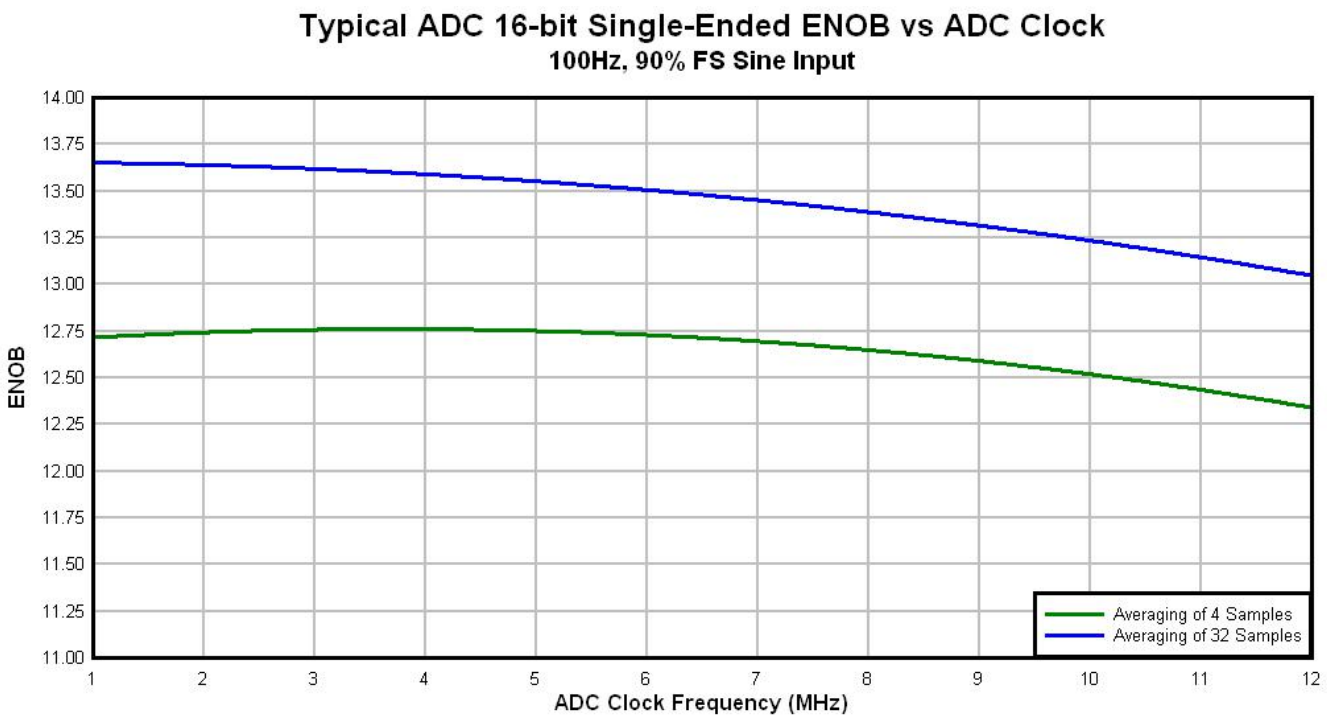


Figure 12. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

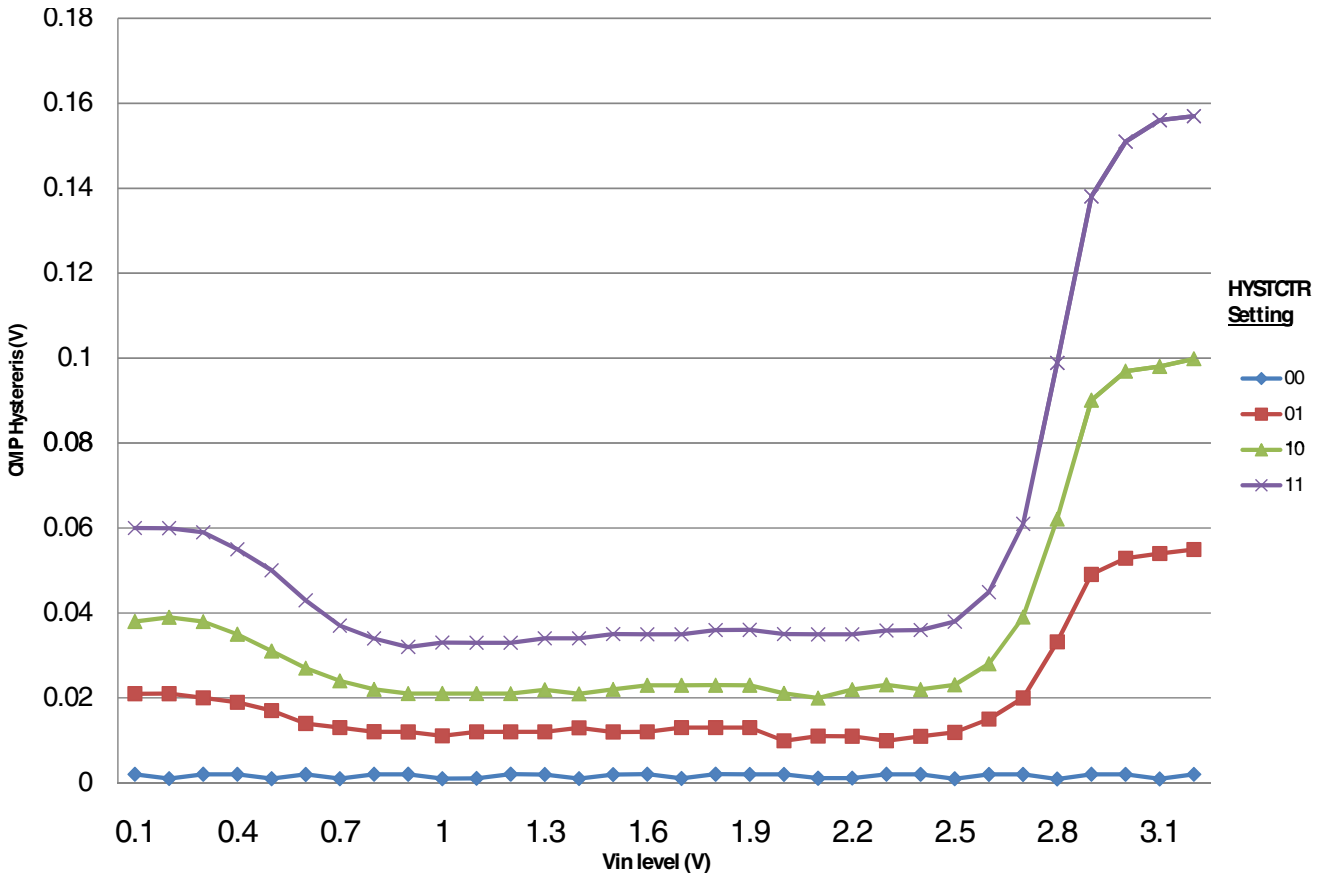


Figure 14. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=1)

6.6.3 Voltage reference electrical specifications

Table 26. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	–40	105	°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 27. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	

Table continues on the next page...

6.8.5.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 34. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

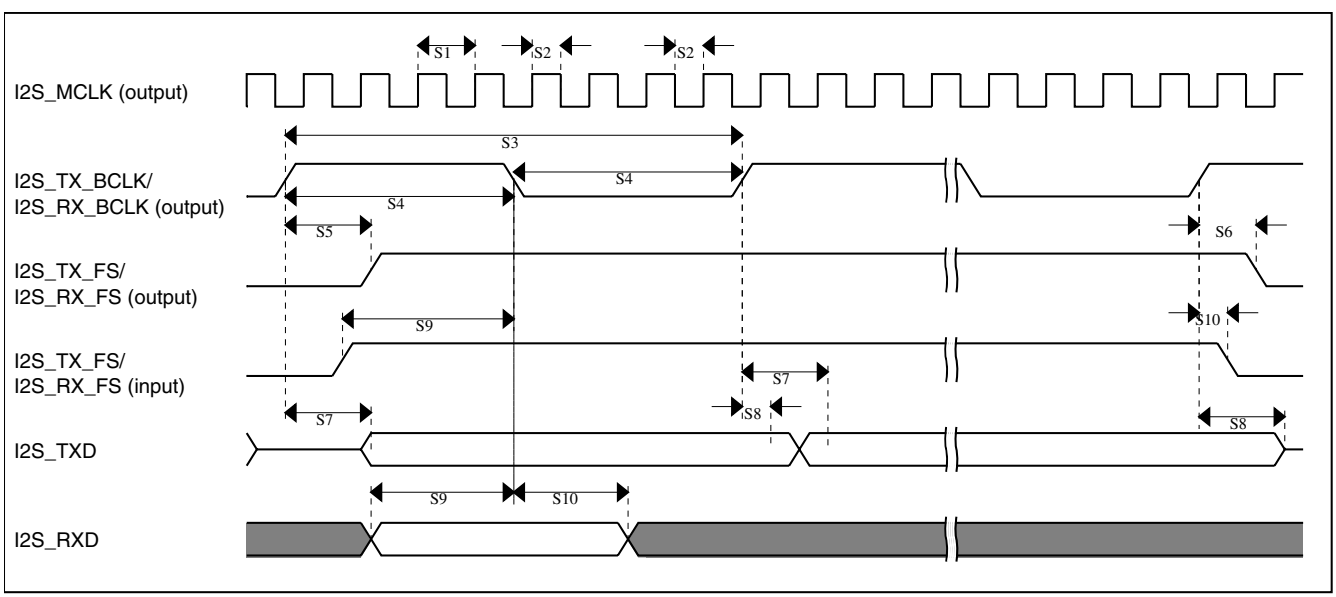


Figure 19. I2S/SAI timing — master modes

Table 38. TSI electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{REFmax}	Reference oscillator frequency	—	8	15	MHz	2, 3
f_{ELEmax}	Electrode oscillator frequency	—	1	1.8	MHz	2, 4
C_{REF}	Internal reference capacitor	—	1	—	pF	
V_{DELTA}	Oscillator delta voltage	—	500	—	mV	2, 5
I_{REF}	Reference oscillator current source base current • 2 µA setting (REFCHRG = 0) • 32 µA setting (REFCHRG = 15)	— —	2 36	3 50	µA	2, 6
I_{ELE}	Electrode oscillator current source base current • 2 µA setting (EXTCHRG = 0) • 32 µA setting (EXTCHRG = 15)	— —	2 36	3 50	µA	2, 7
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	—	fF/count	11
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	µs	12
I_{TSI_RUN}	Current added in run mode	—	55	—	µA	
I_{TSI_LP}	Low power mode current adder	—	1.3	2.5	µA	13

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. Fixed external capacitance of 20 pF.
3. REFCHRG = 2, EXTCHRG=0.
4. REFCHRG = 0, EXTCHRG = 10.
5. V_{DD} = 3.0 V.
6. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
7. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
8. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; Iext = 16.
9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; Iext = 16.
10. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; Iext = 16.
11. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes. Sensitivity depends on the configuration used. The documented values are provided as examples calculated for a specific configuration of operating conditions using the following equation: $(C_{ref} * I_{ext})/(I_{ref} * PS * NSCN)$

    The typical value is calculated with the following configuration:

    $I_{ext} = 6$ µA (EXTCHRG = 2), PS = 128, NSCN = 2, $I_{ref} = 16$ µA (REFCHRG = 7), C_{ref} = 1.0 pF

    The minimum value is calculated with the following configuration:

    $I_{ext} = 2$ µA (EXTCHRG = 0), PS = 128, NSCN = 32, $I_{ref} = 32$ µA (REFCHRG = 15), C_{ref} = 0.5 pF

    The highest possible sensitivity is the minimum value because it represents the smallest possible capacitance that can be measured by a single count.
12. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, EXTCHRG = 7.
13. REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

48 LQFP -QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
40	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN		I2S0_RX_FS				
41	PTD0/ LLWU_P12	DISABLED		PTD0/ LLWU_P12	SPI0_PCS0	UART2_RTS_b					
42	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b					
43	PTD2/ LLWU_P13	DISABLED		PTD2/ LLWU_P13	SPI0_SOUT	UART2_RX					
44	PTD3	DISABLED		PTD3	SPI0_SIN	UART2_TX					
45	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4		EWM_IN		
46	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_ b/ UART0_COL_b	FTM0_CH5		EWM_OUT_b		
47	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6		FTM0_FLT0		
48	PTD7	DISABLED		PTD7	CMT_IRO	UART0_TX	FTM0_CH7		FTM0_FLT1		

8.2 K10 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

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